

WR 10 Bias Tuned Gunn oscillator

Model G 10 (GN10)

The unit utilises a GaAs Gunn device in a waveguide cavity.
The frequency can be adjusted using the applied bias voltage.

The module provides a convenient way of generating an RF signal using a solid state device.
A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

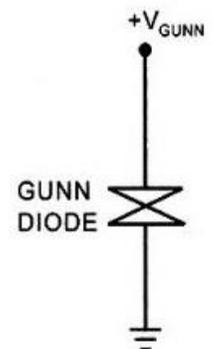
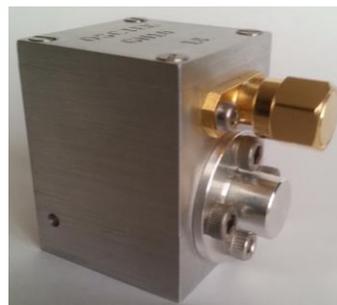
Educational
Communications
Research
Imaging/ Sensors

Frequency	Power		Voltage	Min Bandwidth
(GHz)	mW	dBm	volts	(MHz)
100	5	7	~ + 4.0	100
100	10	10	~ + 4.0	100
100	15	11.8	~ + 4.0	100
100	20	13.0	~ + 4.0	100
100	30	14.8	~ + 4.0	100

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Bias Tuned Gunn oscillator

Model G 10 (GN10)

The unit utilises a GaAs Gunn device in a waveguide cavity.
The frequency can be adjusted using the applied bias voltage.

The module provides a convenient way of generating an RF signal using a solid state device.
A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

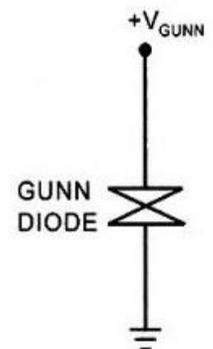
Educational
Communications
Research
Imaging/ Sensors

Frequency	Power		Voltage	Min Bandwidth
(GHz)	mW	dBm	volts	(MHz)
94.0	10	10	~ + 4.4	100
94.0	20	13.0	~ + 4.4	100
94.0	30	15.0	~ + 4.4	100
94.0	40	16.0	~ + 4.4	100
94.0	50	17.0	~ + 4.4	100

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Bias Tuned Gunn oscillator

Model G 10 (GN10)

The unit utilises a GaAs Gunn device in a waveguide cavity.
The frequency can be adjusted using the applied bias voltage.

The module provides a convenient way of generating an RF signal using a solid state device.
A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

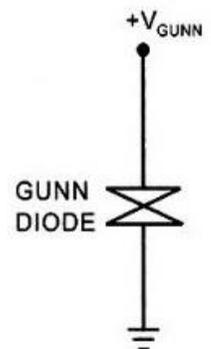
Educational
Communications
Research
Imaging/ Sensors

Frequency	Power		Voltage	Min Bandwidth
(GHz)	mW	dBm	volts	(MHz)
91.5	10	10	~ + 4.5	100
91.5	20	13.0	~ + 4.5	100
91.5	30	15.0	~ + 4.5	100
91.5	40	16.0	~ + 4.5	100
91.5	50	17.0	~ + 4.5	100

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Varactor Tuned Gunn oscillator – Grounded Model G VS10 (G NV10S)

The unit utilises a GaAs Gunn device and a GaAs varactor diode in a waveguide cavity. By appropriate selection the frequency can be altered remotely. This is essentially achieved by the application of a DC tuning voltage which effectively perturbs the electric field within the waveguide cavity.

This circuit is ideal for a robust solution for volume manufacture

The tuning voltage allows a convenient way to alter the frequency of operation; high modulation schemes can be applied thus enabling frequency agility.

A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

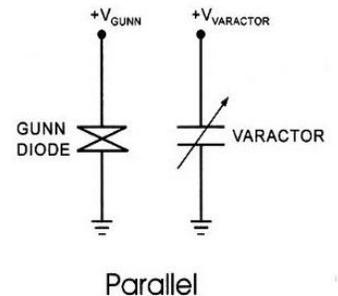
Educational
Communications
Research
Imaging/ Sensors

Frequency (GHz)	Power		Voltage volts	Bandwidth (MHz)		Tuning voltage (volts)
	mW	dBm				
100	5	7	+ 4.0	500	1500	0 to +13 / 15
100	10	10	+ 4.0	500	1250	0 to +13 / 15
100	15	11.8	+ 4.0	500	1000	0 to +13 / 15
100	20	13.0	+ 4.0	500	750	0 to +13 / 15

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Varactor Tuned Gunn oscillator – **Grounded** Model G VS10 (G NV10S)

The unit utilises a GaAs Gunn device and a GaAs varactor diode in a waveguide cavity. By appropriate selection the frequency can be altered remotely. This is essentially achieved by the application of a DC tuning voltage which effectively perturbs the electric field within the waveguide cavity.

This circuit is ideal for a robust solution for volume manufacture

The tuning voltage allows a convenient way to alter the frequency of operation; high modulation schemes can be applied thus enabling frequency agility.

A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

- Educational
- Communications
- Research
- Imaging/ Sensors

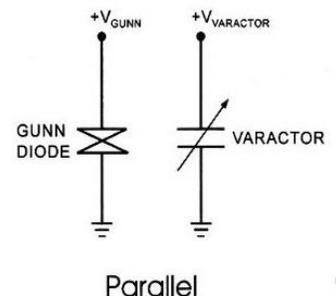
Frequency	Power		Voltage	Bandwidth		Tuning voltage
(GHz)	mW	dBm	volts	(MHz)		(volts)
94	10	10	+ 4.3	500	1500	0 to +13 / 15
94	20	13	+ 4.3	500	1250	0 to +13 / 15
94	30	14.8	+ 4.3	500	1000	0 to +13 / 15
94	40	16.0	+ 4.3	500	750	0 to +13 / 15
94	50	17.0	+ 4.3	400	750	0 to +13 / 15

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female

RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Varactor Tuned Gunn oscillator – Grounded Model G VS10 (G NV10S)

The unit utilises a GaAs Gunn device and a GaAs varactor diode in a waveguide cavity. By appropriate selection the frequency can be altered remotely. This is essentially achieved by the application of a DC tuning voltage which effectively perturbs the electric field within the waveguide cavity.

This circuit is ideal for a robust solution for volume manufacture

The tuning voltage allows a convenient way to alter the frequency of operation; high modulation schemes can be applied thus enabling frequency agility.

A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

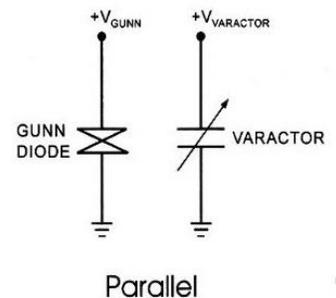
Educational
Communications
Research
Imaging/ Sensors

Frequency (GHz)	Power		Voltage volts	Bandwidth (MHz)		Tuning voltage (volts)
	mW	dBm				
91.5	10	10	+ 4.5	500	1500	0 to +13 / 15
91.5	20	13	+ 4.5	500	1250	0 to +13 / 15
91.5	30	14.8	+ 4.5	500	1000	0 to +13 / 15
91.5	40	16.0	+ 4.5	500	750	0 to +13 / 15
91.5	50	17.0	+ 4.5	400	750	0 to +13 / 15

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Varactor Tuned Gunn oscillator – **Relative Model G V10 (G NV10)**

The unit utilises a GaAs Gunn device and a GaAs varactor diode in a waveguide cavity. By appropriate selection the frequency can be altered remotely. This is essentially achieved by the application of a DC tuning voltage which effectively perturbs the electric field within the waveguide cavity.

This circuit offers a versatile solution where wide bandwidths are required e.g. 6 GHz

The tuning voltage allows a convenient way to alter the frequency of operation; high modulation schemes can be applied thus enabling frequency agility.

A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

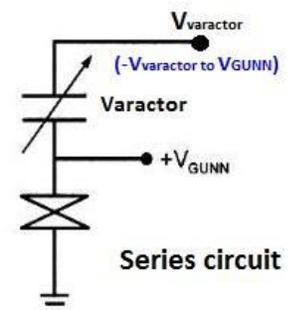
Educational
Communications
Research
Imaging/ Sensors

Frequency	Power		Voltage	Bandwidth		Tuning voltage Relative
(GHz)	mW	dBm	volts	(MHz)		(volts)
100	5	7	+ 4.0	1000	6000	0 to -25
100	10	10	+ 4.0	1000	5000	0 to - 25
100	15	11.8	+ 4.0	1000	3000	0 to -25
100	20	13.0	+ 4.0	500	1000	0 to - 25
100	30	14.8	+ 4.0	500	750	0 to -25

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Varactor Tuned Gunn oscillator – **Relative Model G V10 (G NV10)**

The unit utilises a GaAs Gunn device and a GaAs varactor diode in a waveguide cavity. By appropriate selection the frequency can be altered remotely. This is essentially achieved by the application of a DC tuning voltage which effectively perturbs the electric field within the waveguide cavity.

This circuit offers a versatile solution where wide bandwidths are required e.g. 6 GHz

The tuning voltage allows a convenient way to alter the frequency of operation; high modulation schemes can be applied thus enabling frequency agility.

A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

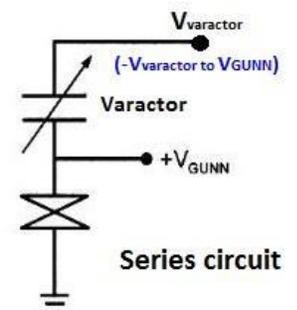
Educational
Communications
Research
Imaging/ Sensors

Frequency (GHz)	Power		Voltage volts	Bandwidth (MHz)		Tuning voltage Relative (volts)
	mW	dBm				
94	5	7	+ 4.3	1000	5000	0 to -25
94	10	10	+ 4.3	1000	4000	0 to - 25
94	15	11.8	+ 4.3	1000	3000	0 to -25
94	20	13.0	+ 4.3	500	1500	0 to - 25
94	30	14.8	+ 4.3	500	1000	0 to -25

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass

WR 10 Varactor Tuned Gunn oscillator – **Relative Model G V10 (G NV10)**

The unit utilises a GaAs Gunn device and a GaAs varactor diode in a waveguide cavity. By appropriate selection the frequency can be altered remotely. This is essentially achieved by the application of a DC tuning voltage which effectively perturbs the electric field within the waveguide cavity.

This circuit offers a versatile solution where wide bandwidths are required e.g. 6 GHz

The tuning voltage allows a convenient way to alter the frequency of operation; high modulation schemes can be applied thus enabling frequency agility.

A clean and stable DC power supply will enhance performance and spectral purity

Applications:-

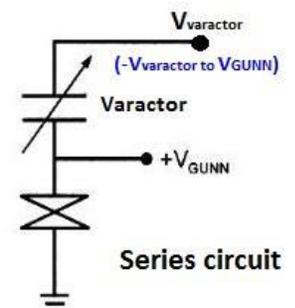
- Educational
- Communications
- Research
- Imaging/ Sensors

Frequency (GHz)	Power		Voltage volts	Bandwidth (MHz)		Tuning voltage Relative (volts)
	mW	dBm				
91.5	5	7	+ 4.3	1000	5000	0 to -25
91.5	10	10	+ 4.3	1000	4000	0 to - 25
91.5	15	11.8	+ 4.3	1000	3000	0 to -25
91.5	20	13.0	+ 4.3	500	1500	0 to - 25
91.5	30	14.8	+ 4.3	500	1000	0 to -25

Alternative centre frequency available.

Specifications at + 32°C case temperature

DC input : SMA female
RF output : UG-387/UM flange compatible



Note: Customised performance and outline envelope available e.g. greater bandwidth, smaller outline/ mass